

# MM5622-01NBX R ideal switch

80 Gbps High-Speed Differential Loopback Switch (DC coupled) RCHS

#### Description

The MM5622-01NBX is a high-speed differential loopback switch (DC coupled) supporting the high-speed differential signal switching required in the latest PCIe Gen 5, Gen 6, SerDes, and other standards. The MM5622-01NBX is based on Menlo Micro's Ideal Switch® technology and can operate at 80 Gbps with a bandwidth of 20 GHz for high-performance applications. The MM5622-01NBX has low insertion loss, fast switching speed, and can operate with greater than 3 billion switching cycles. The MM5622-01NBX system-inpackage (SiP) solution fully integrates the switch driver and charge pump controlled through SPI or GPIO interfaces by a host processor. In addition, integrated decoupling capacitors provide significant board footprint reduction for high-volume production test solutions. The MM5622-01NBX switch provides high data rate for full high-speed differential data applications with unprecedented levels of parallel testing for space-constrained final test and probe test. Applications include chip testing for smartphones, graphics, and network processors, as well as microprocessor, accelerator, and high-speed memory products.

#### **Features**

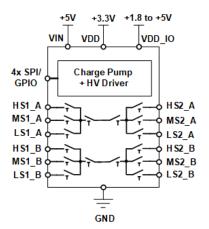
- DC to 20 GHz range •
- Differential Dual DP3T switch with Loopback
- Normally Open, Reflective actuator •
- Low Insertion Loss: -2.2 dB @ 20 GHz
- Integrated charge pump and driver eliminates • the requirement for external biasing and driver circuitry
- Fully controllable ports for low, medium, and high data rate signal routing
- High Reliability: Greater than 3 billion switching • operations
- 8.2 x 8.2 mm LGA Package •

#### **Markets**

- Automated Test Equipment •
- Measurement Equipment •
- Semiconductor Final Package Test •
- Compliance and Loopback Test •

#### Applications

- High-Speed Data Digital Component Testing
- **Optical-Electrical Module Testing**
- **High-Speed Signal Routing** •
- ATE Device Interface Boards .
- **Optical-Electrical Module Testing** •
- **Differential Switch Matrices**





# **Electrical Specifications**

## **Operating Characteristics**

Exceeding the maximum ratings as listed in Table 1 below may reduce the reliability of the device or cause permanent damage. Operation of the MM5622-01NBX should be restricted to the limits indicated in the recommended operating conditions listed in Table 2.

## Electrostatic Discharge (ESD) Safeguards

The MM5622-01NBX is a Class 0 ESD device. When handling the MM5622-01NBX, observe precautions as with any other ESD sensitive device. Do not exceed the voltage ratings specified in Table 1.

Parameter	Symbol	Minimum	Maximum	Unit
DC Supply Voltage	V <sub>DD</sub>	-0.3	3.6	V
I/O Supply Voltage	V <sub>DD_IO</sub>	-0.3	5.5	V
Charge Pump Input	Vin	-0.3	5.5	V
Driver Logic Input Levels		-0.3	$V_{DD_{IO}}$ + 0.3	V
Max Input Voltage Level (RF Pins) <sup>4</sup>		—	3.3	V
Hot Switching Voltage @ 0.5 V <sup>1, 2</sup>		-0.5	0.5	V
Storage Temperature Range <sup>3</sup>		-65	150	٥C
ESD Rating HBM RF Pins <sup>4</sup>		—	150	V
ESD Rating HBM Control and Power Pins⁵		—	2000	V
ESD Rating HBM VPP Pin		_	500	V
Mechanical Shock <sup>6</sup>		—	500	G
Vibration <sup>7</sup>		_	500	Hz

#### Table 1. Absolute Maximum Ratings

#### Notes:

- 1. For hot-switching, differential voltage across switch terminals must be less than or equal to 0.5 V and each switch port must be within +/-0.5 V of RF ground. See section Hot Switch Restrictions.
- 2. RF pins must not be allowed to electrically float during switch operation. See section Floating Node Restrictions for details on avoiding floating nodes.
- 3. See section Storage and Shelf Life more information on shelf and floor life.
- 4. RF pins include: HS1\_x, HS2\_x, MS1\_x, MS2\_x, LS1\_x, LS2\_x.
- 5. Control and power pins include: VIN, VDD, VDD\_IO, PULL\_UP, FLT\_MODE, FLTB, FLIP\_BIT, SCK/CTL1, MOSI/CTL2, MISO/CTL3, SSB/CTL4, CP\_EN.
- 6. See JESD22-B104 for mechanical shock test methodology at 1.0 ms, half-sine, 5 shocks/axis, 6 axis.
- See JESD22-B103 for vibration test methodology at 3.1 G and 30min/cycle, 1 cycle/axis, 3 axis. 7.



Parameter	Symbol	Minimum	Maximum	Unit	Conditions
Charge Pump Power Supply	VIN	4.75	5.5	V	
Driver Logic Supply Voltage	V <sub>DD</sub>	3.0	3.6	V	
Logic Reference Level (VDD_IO)	$V_{\text{DD}\_\text{IO}}$	1.71	5.25	V	
Operating Temperature	TA	-40	85	°C	Ambient
Switch Cycle Frequency		_	100	Hz	

#### **Table 2. Recommended Operating Conditions**

## **Electrical Characteristics**

All specifications valid over full supply voltage and operating temperature range unless otherwise noted. Operating with all analog and digital GND pins connected to system ground (0 V).

Parameter	Symbol	Minimum	Typical	Maximum	Unit	Conditions
Operating Frequency Range		DC	—	20	dB	
Differential Insertion Loss						
HS1 to HS2		—	2.2	—	dB	@20GHz
		—	1.6	—	dB	
MS1 to MS2	SDD <sub>21</sub>	_	2.1		dB	@16GHz
HS1 to MS1		—	0.7	_	dB	
HS2 to MS2		_	0.9	—	dB	
Single-ended Insertion Loss						
LS1A to LS2A		_	2.0	—	dB	
LS1B to LS2B		—	2.5	—	dB	
HS1A to LS1A		—	0.8	—	dB	
HS1B to LS1B		—	0.8	—	dB	
HS2A to LS2A	<b>S</b> <sub>21</sub>	—	1.0	—	dB	
HS2B to LS2B		_	0.9	—	dB	@16GHz
MS1A to LS1A		_	0.6	—	dB	
MS1B to LS1B			0.9			
MS2A to LS2A			0.7		dB	

#### **Table 3. RF Performance Specifications**



Parameter	Symbol	Minimum	Typical	Maximum	Unit	Conditions
MS2B to LS2B			1.0		dB	
Differential Return Loss						
HS1 to HS2		—	20	—	dB	@20GHz
			28		dB	@16GHz
MS1 to MS2	SDD11		23	_	dB	
HS1 to MS1		—	19	—	dB	
HS2 to MS2		—	18	—	dB	
Single-ended Return Loss						
LS1A to LS2A		—	21	—	dB	@16GHz
LS1B to LS2B		—	23	—	dB	
HS1A to LS1A		—	14	_	dB	
HS1B to LS1B		—	21	—	dB	
HS2A to LS2A	S <sub>11</sub>	_	13	—	dB	
HS2B to LS2B		_	20	—	dB	@16GHz
MS1A to LS1A		—	29	_	dB	
MS1B to LS1B		—	13	_	dB	
MS2A to LS2A		—	26	—	dB	
MS2B to LS2B		—	10	_	dB	
Differential Isolation						
HS1 to HS2		_	53	—	dB	@20GHz
		_	57	—	dB	
MS1 to MS2	SDD <sub>21</sub>	—	50	_	dB	@16GHz
HS1 to MS1		—	45	_	dB	
HS2 to MS2		_	51	—	dB	
Single-ended Isolation						
LS1A to LS2A		_	47	—	dB	
LS1B to LS2B		_	61	—	dB	
HS1A to LS1A			40	—	dB	@16GHz
HS1B to LS1B			36		dB	
HS2A to LS2A	<b>S</b> <sub>21</sub>		36	—	dB	
HS2B to LS2B		_	36	_	dB	

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Parameter	Symbol	Minimum	Typical	Maximum	Unit	Conditions
MS1A to LS1A		—	42	—	dB	
MS1B to LS1B		—	35	—	dB	
MS2A to LS2A		—	41	—	dB	
MS2B to LS2B		_	34	_	dB	

#### Notes:

There is phase delay between LSA and LSB signal paths, it may be necessary to match it externally to the MM5622-01NBX device to use any LS related signal paths as a differential pair.



## **Signal Integrity Differential Performance**

Test conditions for the differential PAM4 eye-diagram performance measurements are listed below:

- Analyzed with Physical Layer Test System (PLTS) 2023 •
- Peak to peak input amplitude: 500 mVpp •
- Processed based on a measured S-parameter up to 40GHz •
- Measurements performed at 80 Gbps and 64 Gbps •
- Signal path: (Figure 1 and 2) HS1 to HS2, (Figure 3) MS1 to MS2 •
- Tests performed at ambient temperature •

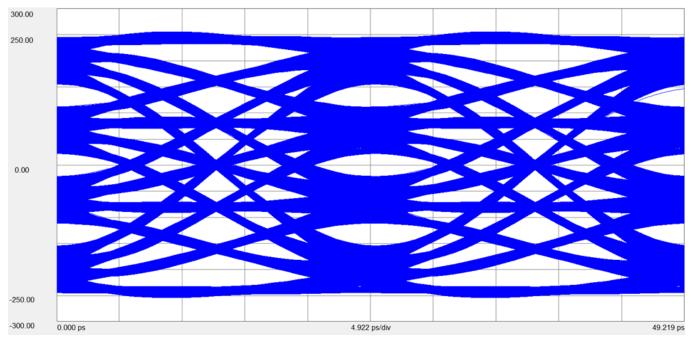
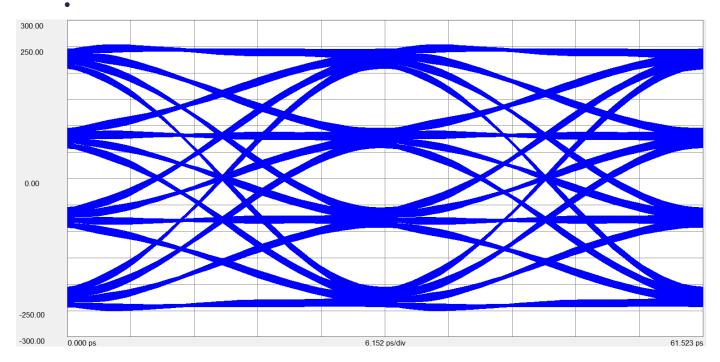


Figure 1. HS1-HS2 Differential PAM4 Eye Diagram (80Gbps)

Еуе	Bit Rate (Gbps)	Eye Height (mV)	Eye Width (ps)	Total Jitter (RMS, ps)
0/1	80	41.0	5	9.0
1/2	80	41.7	7	8.8
2/3	80	41.7	6	9.0







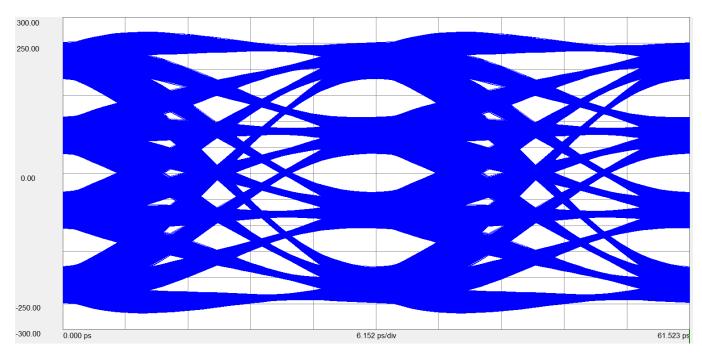
## Figure 2. HS1-HS2 Differential PAM4 Eye Diagram (64Gbps)

#### Table 5. HS1-HS2 Differential PAM4 Eye-Diagram Performance

Еуе	Bit Rate (Gbps)	Eye Height (mV)	Eye Width (ps)	Total Jitter (RMS, ps)
0/1	64	111.8	12	10.3
1/2	64	111.8	16	8.5
2/3	64	111.8	12	10.3



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## Figure 3. MS1-MS2 Differential PAM4 Eye Diagram (64Gbps)

Eye	Bit Rate (Gbps)	Eye Height (mV)	Eye Width (ps)	Total Jitter (RMS, ps)
0/1	64	71.5	9	17.3
1/2	64	71.7	12	10.3
2/3	64	71.8	9	17.4

#### Table 6. MS1-MS2 Differential PAM4 Eye-Diagram Performance



Parameter	Symbol	Minimum	Typical	Maximum	Unit	Conditions
On / Off Switching						Includes settling
Settling time: on			26.5	—	μs	time.
Settling time: off			9	—	μs	
On / Off Switch Operations <sup>2</sup>		3x10 <sup>9</sup>	—	—	Cycles	Specified at 25°C ambient.
Off-State Leakage Current at 30V <sub>DC</sub>		—	7	60	nA	
On-State Resistance	Ron	—	1.7	4.0	Ω	Measured at 30mA DC. HS to MS, HS to LS, MS to LS paths,
			3.4	8.0	Ω	Measured at 30mA DC. HS to HS, MS to MS, LS to LS paths,

#### Table 7. Switch DC and AC Electrical Characteristics<sup>1</sup>

#### Notes:

- 1. DC measurements were performed in single-ended configuration.
- 2. Predicted number of operation cycles as observed on a sample size of 75 units, 100Hz cycle rate, and room temperature with Hot Switch Restrictions.



Parameter	Symbol	Minimum	Typical	Maximum	Unit	Conditions
Charge Pump Power Supply	V <sub>IN</sub>	4.75	5.0	5.5	V	
VIN Current (Dynamic) <sup>1</sup>		—	1.7	2.75	mA	SPI mode, All CH switching at 100Hz
VIN Quiescent Current	IVINQ	—	1.65	2.25	mA	Charge Pump On, All I/O and Channels Static
Low Voltage Logic Supply	V <sub>DD</sub>	3.0	3.3	3.6	V	
VDD UVLO Rising Threshold	UVLORISE	2.77	—	2.95	V	
VDD UVLO Falling Threshold	UVLOFALL	2.72	—	2.90	V	
Low Voltage Digital Current <sup>1</sup>	IDD	—	520	700	μA	SPI mode, All CH Switching at 100Hz
Low Voltage Digital Quiescent Current	Iddq	—	480	550	μA	Charge Pump On, All I/O & Channels Static
Low Voltage Digital Sleep Mode Current	IDDSLEEP		<1	10	μA	Charge Pump Off, SPI and Inputs in Static State
Logic Reference Level	Vdd_10	1.71	—	5.25	V	
I/O Logic Supply Current		—	<10	50	uA	All Channels Switching at 100Hz
Notes:						

#### **Table 8. Power Supply Specifications**

1. Specification is obtained by characterization.



Parameter	Symbol	Minimum	Typical	Maximum	Unit	Conditions
Logic I/O Level High	I/O∨н	0.7 x V <sub>DD_10</sub>	_	V <sub>DD_IO</sub>	V	
Logic I/O Level Low	I/O <sub>VL</sub>	0	—	0.3 x V <sub>DD_10</sub>	V	
Logic I/O Hysteresis (SCK only) <sup>1</sup>	I/O <sub>VH</sub>	_	0.25	—	V	
Digital Input Capacitance	C <sub>IN</sub>	—	2	5	pF	
SDO Load Capacitance <sup>2 3</sup>	C <sub>SDO</sub>	—	—	10	pF	
SDO Source Current @ VDD_IO <sup>1</sup> :	Isdoh					VOUT = 0.8 x VDD_IO
5 V		180	290	—	mA	
3.3V 1.8V		75	140	—	mA	
1.0V		20	35	—	mA	
SDO Sink Current @ VDD_IO <sup>1</sup> :	I <sub>SDOL</sub>					VOUT = 0.2 x VDD_IO
5.0 V		140	260	—	mA	
3.3 V 1.8 V		65	140	—	mA	
1.8 V		20	40	<u> </u>	mA	
Pull down resistor at SDI, SCK, SSB, CP_EN, FLIP_BIT, and FLT_MODE pins	Rpd	120	200	280	kΩ	SSB pull down is only in GPIO mode
CP_EN pin toggle low time	T <sub>TOGGLE</sub>	500	_	_	ns	Minimum time CP_EN has to be held low to restart the IC from fault condition
FLTB pin max sink current <sup>1</sup>		65	140	—	mA	FLTB = GND VDD_IO=3.3V

#### Table 9. Digital Interface AC and DC Specifications

#### Notes:

- 1. Specification is obtained by characterization.
- 2. Specification is for design guidance only.
- SDO load capacitance = input capacitance of SDI pin + trace capacitance from SDO to SDI 3.



Parameter	Symbol	Minimum	Typical	Maximum	Unit	Conditions
SPI Clock Frequency	SCK	-	_	33	MHz	
SDI Valid to SCK Setup Time <sup>1</sup>	ts∪	2	—	—	ns	
SDI Valid to SCK Hold Time <sup>1</sup>	t <sub>HD</sub>	5	—	_	ns	
SCK High Time <sup>1</sup>	tнı	15.5	_	_	ns	
SCK Low Time <sup>1</sup>	t∟o	15.5	—	_	ns	
SSB Pulse Width <sup>1</sup>	tсsн	15	—	—	ns	
LSB SCK to SSB High <sup>1</sup>	<b>t</b> CSHLD	15	—	—	ns	
SSB Low to SCK High <sup>1</sup>	tcssu	15	—	—	ns	
SDO Propagation Delay from SCK Falling Edge <sup>1</sup>	t <sub>SDOH</sub>	10	—	_	ns	
SDO Output Valid after SSB Low <sup>1</sup>	tcsdo	20	—	_	ns	
SSB Inactive to SDO High Impedance <sup>1</sup>	tsdoz	_	_	10	ns	
Notes: 1. Specification is obta	ained by chara	cterization.				

## Table 10. Digital Interface Timing Specifications

Parameter	Symbol	Minimum	Typical	Maximum	Unit	Conditions		
Power-On- Reset <sup>1</sup>	POR	_	1.25	2.5	ms	Time for logic input signals to be considered valid after application of VIN and VDD.		
Start-Up Time	Tst	—	20	33	ms	CP_EN=1 (CPEN bit=1) to VPP rises to 90% of set value		
Notes:								
1. Specification	1. Specification is for design guidance only.							

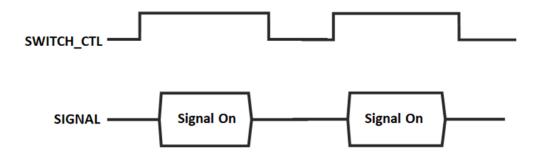
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## Hot Switch Restrictions

The MM5622-01NBX is not intended for hot switching applications and care should be taken to insure that switching occurs at less than 0.5 V. Further, the voltage at the switch terminals must be within +/-0.5 V relative to signal ground.



## **Floating Node Restrictions**

RF pins must not be allowed to electrically float during switch operation and therefore require some form of DC path to ground to prevent charge accumulation. The MM5622-01NBX uses the superport configuration for improved high frequency performance. See Menlo Micro application note Avoiding Floating Nodes for a detailed explanation of the hazard conditions to avoid and recommended solutions.



## **Functional Block Diagram**

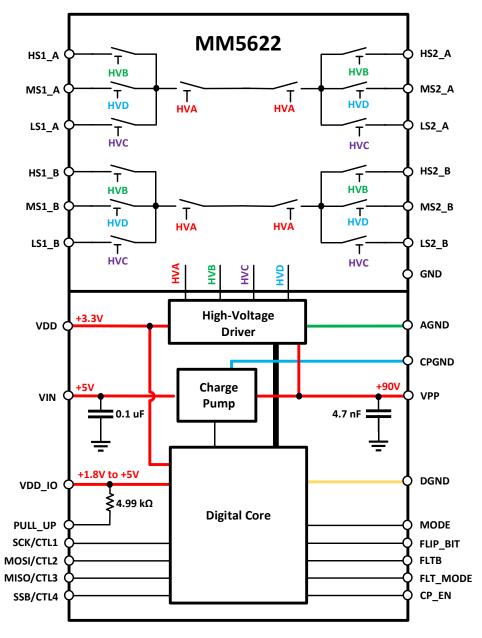


Figure 4. Functional Block Diagram



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# **Package / Pinout Information**

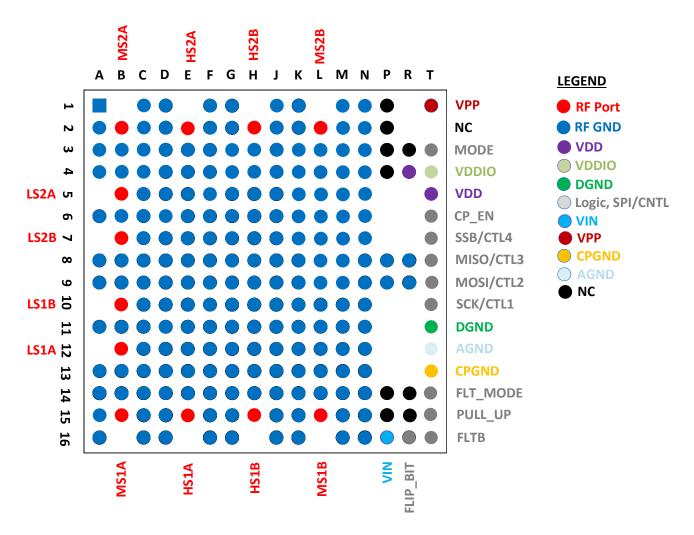


Figure 5. Package Pinout (Top View/As Mounted)

See Table for detailed pin descriptions.



D's Name	D'	<b></b>
Pin Name	Pin #	Description
HS1A	E15	Port 1A of the high-speed signal path. Can be used as an input or an output.
HS1B	H15	Port 1B of the high-speed signal path. Can be used as an input or an output.
MS1A	B15	Port 1A of the medium-speed signal path. Can be used as an input or an output.
MS1B	L15	Port 1B of the medium-speed signal path. Can be used as an input or an output.
LS1A	B12	Port 1A of the low-speed signal path. Can be used as an input or an output.
LS1B	B10	Port 1B of the low-speed signal path. Can be used as an input or an output.
HS2A	E2	Port 2A of the high-speed signal path. Can be used as an input or an output.
HS2B	H2	Port 2B of the high-speed signal path. Can be used as an input or an output.
MS2A	B2	Port 2A of the medium-speed signal path. Can be used as an input or an output.
MS2B	L2	Port 2B of the medium-speed signal path. Can be used as an input or an output.
LS2A	B5	Port 2A of the low-speed signal path. Can be used as an input or an output.
LS2B	B7	Port 2B of the low-speed signal path. Can be used as an input or an output.
SCK/CTL1	T10	Clock input in SPI mode; RF channel control in GPIO mode. Has an internal pull-down resistor.
MOSI/CTL2	Т9	SPI data input (SDI) in SPI mode; RF channel control in GPIO mode. Has an internal pull-down resistor.
MISO/CTL3	Т8	SPI data output (SDO) in SPI mode; RF channel control in GPIO mode. Has an internal pull-down resistor.
SSB/CTL4	Τ7	Chip select in SPI mode; RF channel control in GPIO mode. Has an internal pull-up resistor in SPI mode, and an internal pull- down resistor in GPIO mode.

## Table 12. Detailed Pin Description



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Pin Name	Pin #	Description
FLT_MODE	T14	Fault Mode select in GPIO mode. Fault Mode is disabled if high. Has a built-in pull-down resistor. Pin is ignored in SPI mode.
FLTB	T16	Fault indicator in GPIO and SPI modes. Open drain output to allow "Wire-OR" of multiple ICs. Goes low when a fault is detected. Can be left open if not used. Pull- up voltage must be ≤ VDD_IO.
FLIP_BIT	R16	This pin has an internal pull-down resistor. In SPI mode, this pin should be tied to VDD_IO. In GPIO mode FLIP_BIT should be tied to GND.
MODE	Т3	Logic level input to switch inputs between SPI and GPIO modes. MODE = 0 is SPI mode. MODE=1 is GPIO mode.
CP_EN	Τ6	Charge pump enable pin in GPIO mode. Pull-up to VDD_IO to enable the charge pump. Has a built-in pull-down resistor. Pin is ignored in SPI mode.
VDD	R4, T5	3.3 V nominal input to digital logic and internal level translators. Bypass with a low ESR 1 $\mu$ F ceramic capacitor.
VDD_IO	Τ4	For 3.3 V nominal digital I/O levels, connect to VDD. For alternate I/O levels, connect to a separate supply (+1.8V to +5.0V). Bypass with a low ESR 1 $\mu$ F ceramic capacitor if separate from VDD.
PULL_UP	T15	Connect this pin directly to the FLTB. Has a built-in 4.99 k $\Omega$ resistor to VDD_IO.
DGND	R3, T11	Digital ground, should be connected to PCB ground. The R3 pin has an internal pull-down resistor, it can be left floating.
VIN	P16	Connect to 5 V power supply. Bypass with a low ESR 1 $\mu$ F ceramic capacitor.
CPGND	T13	Charge pump ground, should be connected to PCB ground.
VPP	T1	High-voltage (90V) charge pump output. Leave this pin unconnected.
AGND	T12	Analog ground, should be connected to PCB ground.



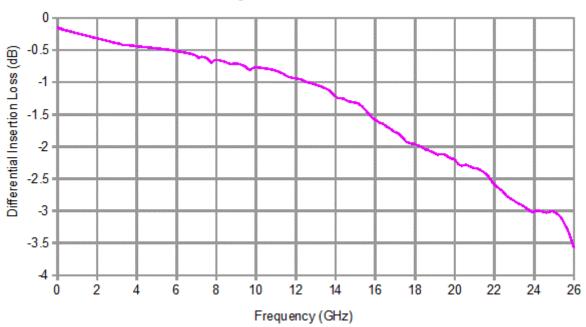
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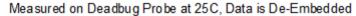
Pin Name	Pin #	Description
GND	A1,C1,D1,F1,G1,J1,K1,M1,N1, A2,C2,D2,F2,G2,J2,K2,M2,N2, A3,B3,C3,D3,E3,F3,G3,H3,J3,K3,L3,M3,N3, A4,B4,C4,D4,E4,F4,G4,H4,J4,K4,L4,M4,N4, C5,D5,E5,F5,G5,H5,J5,K5,L5,M5,N5, A6,B6,C6,D6,E6,F6,G6,H6,J6,K6,L6,M6,N6, C7,D7,E7,F7,G7,H7,J7,K7,L7,M7,N7, A8,B8,C8,D8,E8,F8,G8,H8,J8,K8,L8,M8,N8, P8,R8, A9,B9,C9,D9,E9,F9,G9,H9,J9,K9,L9,M9,N9, P9,R9, C10,D10,E10,F10,G10,H10,J10,K10,L10, M10,N10, A11,B11,C11,D11,E11,F11,G11,H11,J11, K11,L11,M11,N11, C12,D12,E12,F12,G12,H12,J12,K12,L12, M12,N12, A13,B13,C13,D13,E13,F13,G13,H13,J13, K13,L13,M13,N13, A14,B14,C14,D14,E14,F14,G14,H14,J14, K14,L14,M14,N14, A15,C15,D15,F15,G15,J15,K15,M15,N15, A16,C16,D16,F16,G16,J16,K16,M16,N16	Connect to common ground. These pins are internally connected to the RF ground reference.



# **RF** Performance

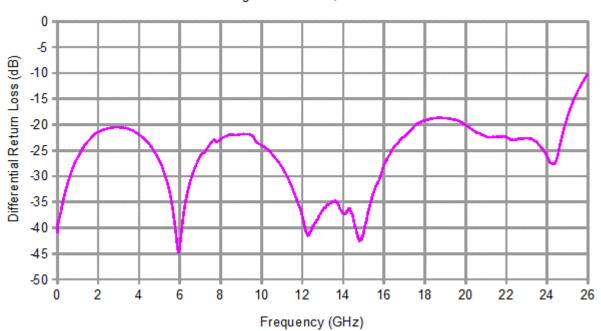
Typical device performance, measured on MM5622-01NBX EVK at room temperature.











Measured on Deadbug Probe at 25C, Data is De-Embedded

Figure 7. Return Loss/SDD11



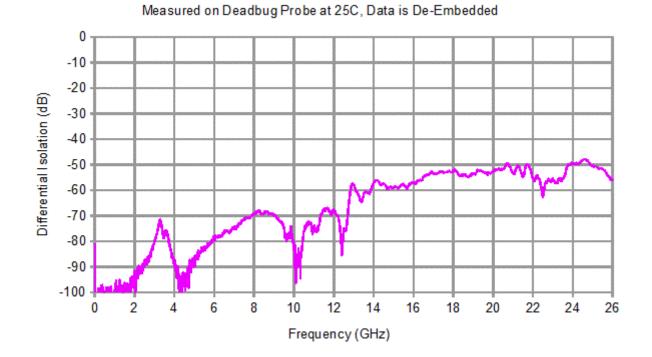


Figure 8. Isolation/SDD21



# Programming

## **Communication Interface**

The MM5622-01NBX has two modes of operation; **SPI (serial)** and **GPIO (Parallel)**, selected by the **MODE** input pin.

All the SPI pins (except SSB pin), the FLIP\_BIT, the FLT\_MODE pin, and the CP\_EN pin have an internal pull-down resistor to ensure that no digital input pins are left floating.

The SSB pin has a pull-up current source in SPI mode. This ensures that the IC defaults to a disabled state in SPI mode. In GPIO mode, this pin is CTL4. In this case, the SSB pin has a pull-down resistor. This ensures that the input is low by default in GPIO mode.

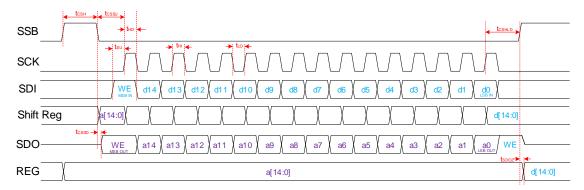


Figure 9. SPI Timing Diagram

#### **Serial Communication**

MODE = 0, activates the 16-Bit Serial Peripheral Interface (SPI) module for operation. Multiple devices can be daisy-chained to drive multiple ICs using one SPI bus (see <u>Daisy Chain Operation</u>, <u>Figure 12.</u>, <u>Figure</u>, and <u>Figure</u>). The SPI works at any frequency up to a maximum of 33 MHz and may operate at significantly lower frequencies if the logic signals adhere to the data setup and hold requirements.

#### **SPI Interface Mode**

SPI timing diagrams are provided in Figures 10 to Figure 14. In SPI mode, data transmission starts when SSB goes Low, causing the Target to output the Most Significant Bit (MSB) of data to the SDO (MISO) pin. Data transfer from Host to Target takes place during the rising edge of the clock (SCK), which is idle when SSB is High. This mode of operation requires data for Host and Target to be present on SDI (MOSI) before the rising edge of the clock (defining SDI to SCK setup time). Data is pushed out of the SDO (MISO) pin during the falling edge of the clock. After the first 16-bit transaction, Host writes the latest data (DN) to Target, while Target passes its previous (DN-1) stored data to the Host. Data is latched into the internal



registers at the rising edge of SSB, if WR\_EN = 1.

#### **SPI Data Format**

SPI data is sent in a 16-bit format. The first MSB bit (WE), if high, enables the Write mode. The following 7 MSB bits hold the Control and Fault Status bits. The 8 LSB bits hold the Switch State bits.

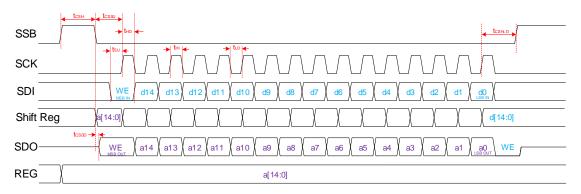


Figure 10. SPI Read Only (1 IC, No Daisy Chain)

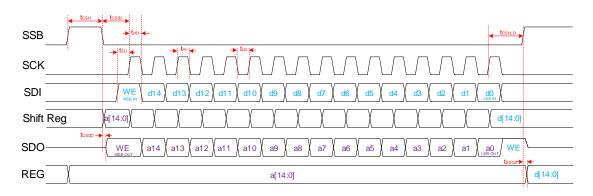


Figure 11. SPI Read & Write (1 IC, No Daisy Chain)



#### SPI Control Registers

The SPI interface provides access to two 8-bit Internal Registers: Register STATE and Register CONTROL that are Read/Write registers. Register data is read by toggling SSB low and monitoring the data at the SDO pin while clocking the SCK pin. Register STATE holds the state of the 4 internal high-voltage outputs and is updated when SSB goes from LOW to HIGH, if the Write Enable bit is high.

Register CONTROL holds four control bits (CPEN, VPPCOMP, FLT\_MODE, and SLEEP), and the fault status bit (FSTAT). The MSB bit enables the Write mode if high. In SPI mode, the CP\_EN and FLT\_MODE pins are ignored. Settings in the CONTROL register are used instead.

Note: The first row of the register tables below shows the read/write type, and default state. At power-on-reset (POR), all bits in both registers are set to LOW internally.

#### **State Register**

R/W - 0	R/W - 0	R/W - 0	R/W - 0	R/W - 0	R/W - 0	R/W - 0	R/W – 0
0	0	0	0	HVD	HVC	HVB	HVA
bit7							bit 0
bit 7: Low							
	this bit low.						
bit 6: <b>Low</b>							
Set t	this bit low.						
bit 5: <b>Low</b>							
Set t	this bit low.						
bit 4: <b>Low</b>							
	this bit low.						
bit 3: HVD							
	HVD Output is						
	HVD Output is	Disabled (Lov	N)				
bit 2: HVC							
1 = H	HVC Output is	Enabled (Hig	h)				
0 = HVC Output is Disabled (Low)							
bit 1: <b>HVB</b>							
1 = HVB Output is Enabled (High)							
0 = HVB Output is Disabled (Low)							
bit 0: HVA							
1 = H	-IVA Output is	Enabled (Higl	h)				
	-IVA Output is						



#### **Control Register**

R/W - 0	R/W – 0						
WR_EN	FSTAT	SLEEP	FLTMODE	VPPCOMP	Х	CPEN	Х
bit7							bit 0

bit 7: WR\_EN

1 = Enable write mode

0 = Disable Write mode (read only)

bit 6: FSTAT (see Note 1 below)

1 = VPP OR VDD Fault status = faulted

0 = VPP OR VDD Fault status = NOT faulted

bit 5: SLEEP

1 = SLEEP mode active (all analog circuits disabled)

- 0 = SLEEP mode inactive (all analog circuits enabled)
- bit 4: FLTMODE

1 = Fault Mode Disabled (shutdown Disabled)

0 = Fault Mode Enabled (shutdown Enabled)

bit 3: VPPCOMP

1 = VPP under-voltage comparator is disabled.

- 0 = VPP under-voltage comparator is active.
- bit 2: Do Not Care

This bit can be set to either state without effecting performance.

bit 1: CPEN

1 = Charge Pump is enabled

0 = Charge Pump is disabled

#### bit 0: Do Not Care

This bit can be set to either state without effecting performance.

#### Notes:

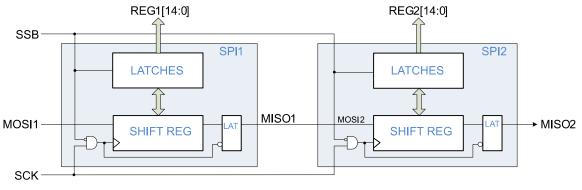
1. After this bit is set high, it must be written to 0 to clear the fault. If fault mode is enabled, CPEN must be toggled to restart the charge pump. See Fault Conditions for more information.



#### **Daisy Chain Operation**

REG2

Daisy chaining the ICs is permitted and involves connecting the MISO of one chip to the MOSI of the next chip in the chain, as shown in <u>Figure 12</u>. SPI timing diagrams with daisy-chained devices are provided in <u>Figure 14</u>.



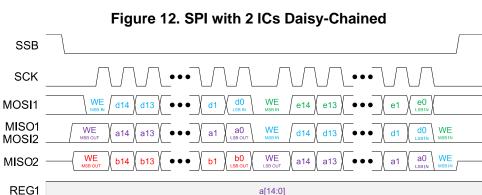
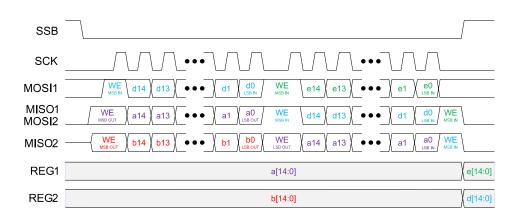


Figure 13. SPI Read Only (2 ICs Daisy-chained)

b[14:0]





#### Figure 14. SPI Read & Write (2 ICs Daisy-Chained)

## **GPIO** Communication

MODE = 1 and FLIP\_BIT = 0 activates the GPIO (General Purpose Input Output or Parallel) Communication Mode. In this mode of operation, the SPI Interface pins act as parallel inputs, as described in <u>Table 12</u>. <u>Detailed Pin Description</u>. Valid switch states are listed here.

		Inpu	t Signal	s			HVOUT			
Count	FLIP_BIT	CTL4	CTL3	CTL2	CTL1	D	с	В	А	Switch State
0	0	0	0	0	0	OFF	OFF	OFF	OFF	ALL OFF (OPEN)
1	0	0	0	0	1	OFF	OFF	OFF	ON	
2	0	0	0	1	0	OFF	OFF	ON	OFF	
3	0	0	0	1	1	OFF	OFF	ON	ON	HS1 – HS2
4	0	0	1	0	0	OFF	ON	OFF	OFF	
5	0	0	1	0	1	OFF	ON	OFF	ON	LS1 – LS2
6	0	0	1	1	0	OFF	ON	ON	OFF	HS1 – LS1 and HS2 – LS2
7	0	0	1	1	1	OFF	ON	ON	ON	
8	0	1	0	0	0	ON	OFF	OFF	OFF	
9	0	1	0	0	1	ON	OFF	OFF	ON	MS1 – MS2
10	0	1	0	1	0	ON	OFF	ON	OFF	HS1 – MS1 and HS2 – MS2
11	0	1	0	1	1	ON	OFF	ON	ON	
12	0	1	1	0	0	ON	ON	OFF	OFF	MS1 – LS1 and MS2 – LS2
13	0	1	1	0	1	ON	ON	OFF	ON	
14	0	1	1	1	0	ON	ON	ON	OFF	
15	0	1	1	1	1	ON	ON	ON	ON	ALL ON (CLOSED)

#### Table 13. State Table in GPIO Mode



## **Fault Conditions**

There are two comparators that can signal a fault condition - VDD under voltage fault and VPP under voltage fault. Faults are reported differently depending on the mode of communication - SPI or GPIO.

**Note:** The VPP under voltage comparator can be disabled. In SPI mode, it is disabled when the VPPCOMP bit in the CONTROL register is high. In GPIO mode, the comparator is disabled when CP\_EN pin is set low.

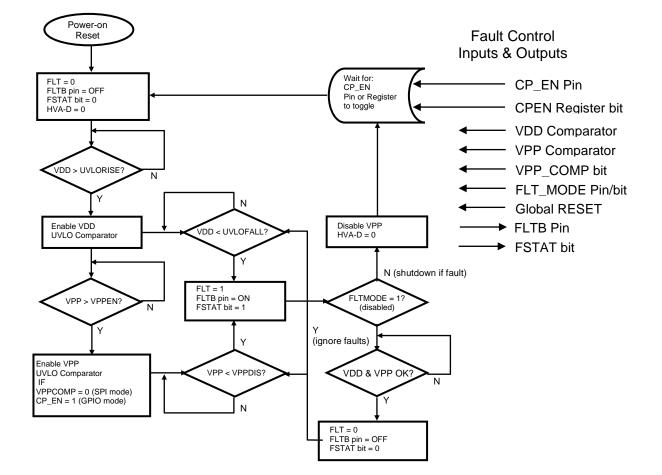
The outputs of the VDD and VPP fault comparators are logically OR'ed. The output of the OR gate controls the FLTB pin. FLTB is an open-drain output and is ON (low impedance) if either fault is detected. In SPI mode, bit 6 of the CONTROL register provides VDD and VPP fault status.

At start-up, the FLTB pin is held OFF (high impedance). It is allowed to change state only after each voltage goes past its Enable threshold (VDD goes higher than UVLO<sub>RISE</sub> and VPP goes higher than V<sub>EN</sub>). This prevents a race condition at startup.

Once VDD and VPP go above their thresholds, the comparators monitoring VDD and VPP actively monitor for faults. If VDD goes below UVLO<sub>FALL</sub> or VPP goes below VPP<sub>DIS</sub>, a fault condition is signaled by setting the FLTB pin low and the Fault Status bit high (bit 6 in the CONTROL register). The FLTB pin returns to an open state when the fault condition is cleared and the FSTAT bit remains latched high until it is cleared via a SPI write. If Fault Mode is enabled (in GPIO mode, FLT\_MODE pin = 0, in SPI mode, FLT\_MODE bit = 0), the internal high-voltage outputs are all set low (all switches open) and the charge pump is turned off. The user must toggle the CP\_EN pin (GPIO mode) or the CPEN register bit (SPI mode) low and then high to restart the device.

If Fault Mode is disabled (in GPIO mode, FLT\_MODE pin = 1; in SPI mode, FLT\_MODE bit = 1), no action is taken by the IC. The fault condition is reported but does not affect the charge pump operation or switch states.







#### Notes:

- 1. The un-faulted supply continues to be monitored when a fault occurs. The FLT signal remains faulted until both supplies are above their brownout trip level.
- 2. VDD\_IO is not monitored unless it is connected to VDD.
- 3. VPP is not monitored if: VPPCOMP = 1 in SPI mode OR the CP\_EN pin is low In GPIO mode.



# **Application Circuit Diagram**

Figure 16, Figure ,and Figure 18 show a few MM5622-01NBX application diagrams. For additional applications, refer to the MM5622-01NBX Application Notes.

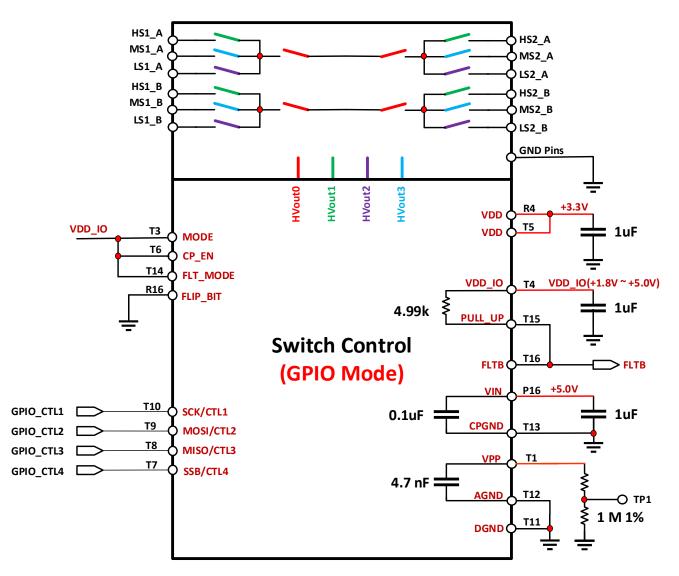


Figure 16. External Circuits for GPIO Mode



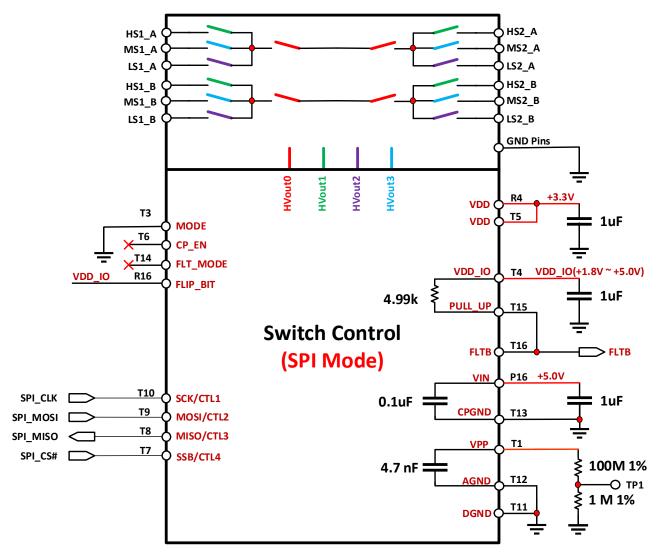


Figure 17. External Circuits for SPI Mode



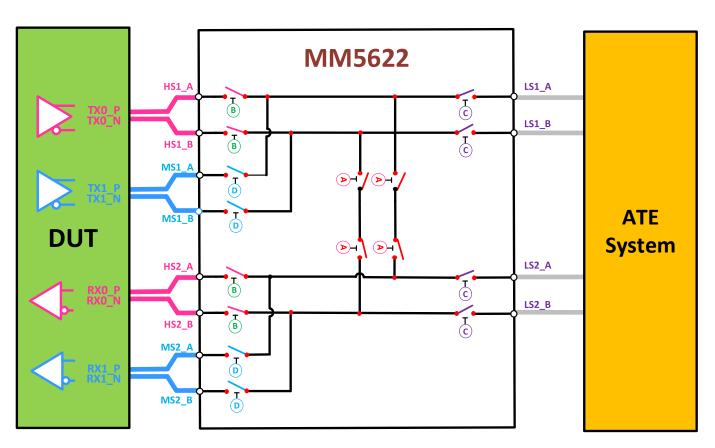


Figure 18. Double-Density HSIO Loopback Mode Test



# **Package Drawing**

Figure shows the 8.2 mm x 8.2 mm 227P LGA package drawing. All dimensions are given in millimeters.

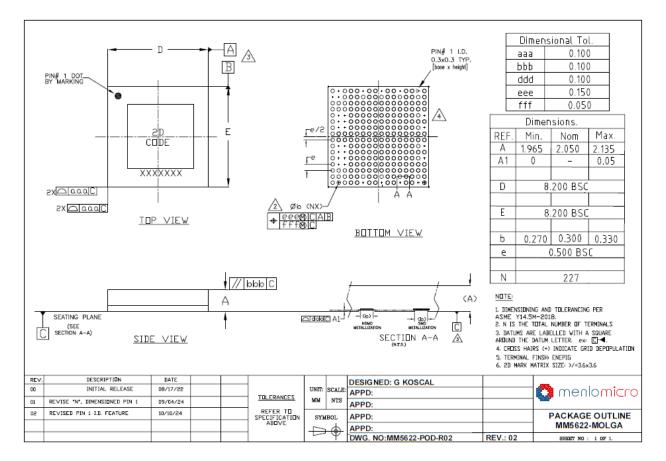


Figure 19. Package Drawing



# MM5622-01NBX EVK PCB Layout

Figure shows the PCB layout based on the MM5622-01NBX EVK stack-up.

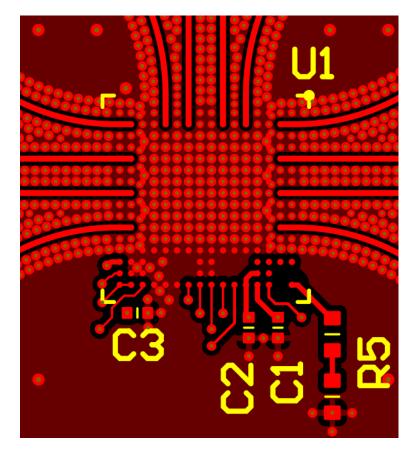


Figure 20. MM5622-01NBX EVK PCB Layout

Please contact your local Menlo Micro sales support for further information.



# **Recommended Solder Reflow Profile**

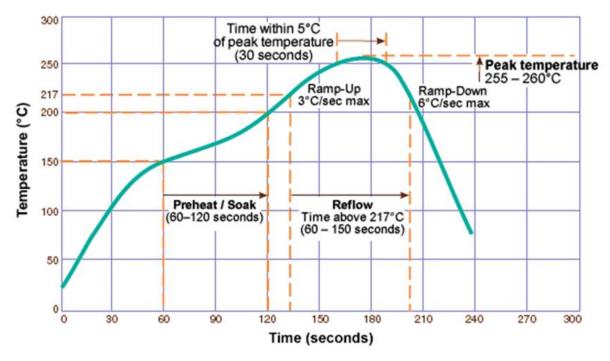


Figure 21. Reflow Profile

Reflow profiles and assembly guidelines are given for RoHS-compliant (lead-free) solder alloy.

Follow Moisture Sensitivity Level (MSL) 3 handling precautions specified in IPC/JEDEC J-STD-020.

## **Storage and Shelf Life**

Under typical industry storage conditions (≤30 °C/60% RH) in Moisture Barrier Bags, the following is recommended:

- Customer Shelf Life: 24 months from customer receipt date. •
- Extended Shelf Life: 60 months from customer receipt date if re-bagged every 24 months or less. •



# **Package Marking Information**

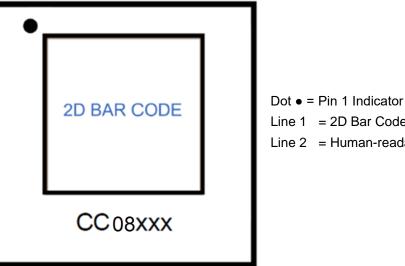
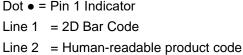


Figure 22. Package Marking Drawing





# **Package Options and Ordering Information**

All Menlo Micro solutions are EAR99 compliant.

Part Number	Package Description	Temp Range	Device Marking <sup>1</sup>			
MM5622-01NBX	Dual DP3T w/internal charge pump - DC coupled loopback high-speed 80Gbps - 8.2mm x 8.2mm LGA Industrial Temperature	-40C to +85C	CC-08xxx			
MM5622-01NBX-TR	Dual DP3T w/internal charge pump - DC coupled loopback high-speed 80Gbps - 8.2mm x 8.2mm LGA Industrial Temperature Tape and Reel (Qty 250)	-40C to +85C	CC08xxx			
MM5622EVK3A	High-performance evaluation board for MM5622-01NBX (Dual DP3T w/internal charge pump-DC coupled loopback, w/SV Microwave connectors-QTY-24), DC-80 Gbps - 8.2mmx8.2mm LGA					
MM5622EVK3B	High-performance evaluation boar charge pump-DC coupled loopbac 80 Gbps - 8.2mm x8.2mm LGA					

#### Notes:

1. Additional markings may be present, including logo or lot trace code information. This information may be a 2D barcode or other human-readable markings. Note that 'x' is a placeholder for a 5-digit numerical code.

Bulk	Tape and Reel <sup>1</sup>
MM5622-01NBX	MM5622-01NBX-TR
Notes:	

1. 250pcs standard tape and reel increment.



# **Important Information**

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For product technical questions and application information: support@menlomicro.com.